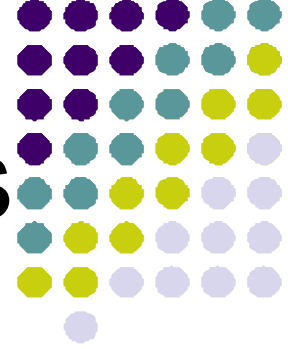


State Variable Equations



$$\varepsilon_{ij} = \varepsilon^E_{ij} + \int_0^t \dot{\varepsilon}^I_{ij} d\tau + \varepsilon^{TH}_{ij} \quad \textit{Kinematic}$$

$$\dot{\varepsilon}^I_{ij} = \left| \dot{\varepsilon}^I_0 \left(\sigma_{kl}, T, P, f_p, \zeta_r, \dots \right) \right|_{ij} \quad \textit{Kinetic}$$

$$\zeta_m = \zeta_m \left(\dot{\varepsilon}^I_{ij}, \sigma_{kl}, P, T, f_p, \zeta_s, \dots \right) \quad \textit{Evolution}$$

Stouffer and Dame, "Inelastic deformation of metals", 1996

Apparent (Empirical) Activation Parameters

$$\dot{\varepsilon} = \dot{\varepsilon}_0 \sigma^n \exp\left(-\frac{\Delta H}{RT}\right)$$

$$n = \left. \frac{\partial \ln \dot{\varepsilon}}{\partial \ln \sigma} \right|_{T, P, \dots}$$

Stress exponent

$$V^* \triangleq \left. \frac{\partial \ln \dot{\varepsilon}}{\partial P} \right|_{T, \sigma, \dots}$$

Activation Volume

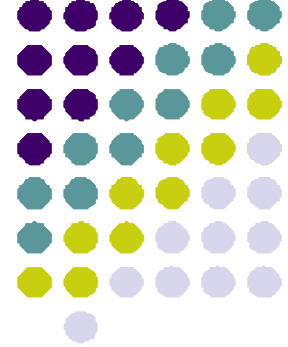
$$H^* \triangleq \left. \frac{\partial \ln \dot{\varepsilon}}{\partial (1/T)} \right|_{\sigma, P, \dots}$$

Activation { Energy
Enthalpy

$$A^* \triangleq \left. \frac{1}{b} \frac{\partial \ln \dot{\varepsilon}}{\partial (\sigma)} \right|_{P, T, \dots}$$

Activation { Volume
Area

Orowan's Equation (Kinetic Equation)



Egon Orowan

Egon Orowan 1966 as a Visiting Scientist at the Boeing Scientific Research Laboratory in Seattle, Washington.

Generation

Recovery

Recrystallization

$$\dot{\epsilon} = \rho_m |\mathbf{b}| v$$

A purple arrow points from the word "Recrystallization" to the term ρ_m in the equation. A blue arrow points from the word "Lattice Friction" to the term v in the equation.

Lattice Friction

Precipitates

Dislocation Interactions

Source/Sink

Frank-Read Source

- Force balance gives

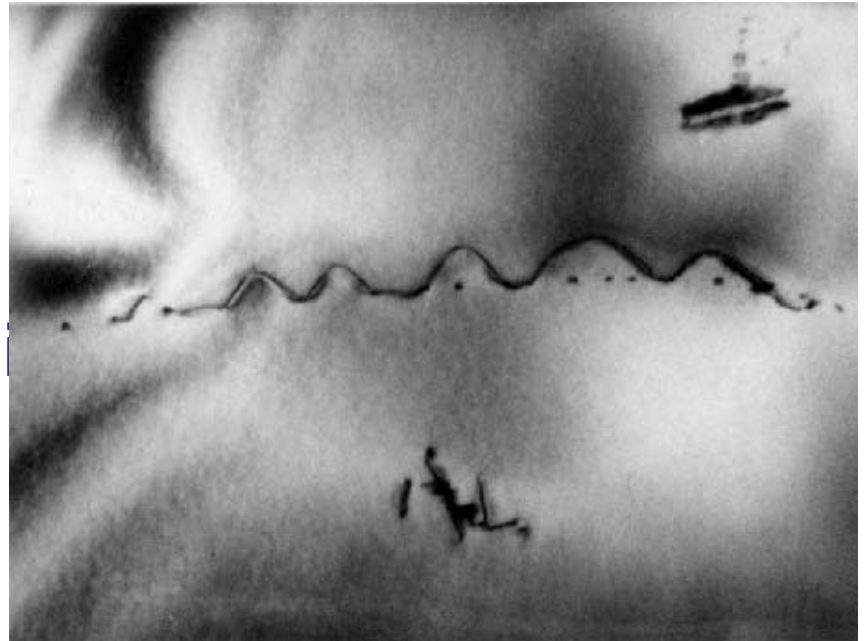
$$\sigma = \frac{\mu b}{2R}$$

- The dislocation density

$$L = \rho^{-1/2}$$

- Then

$$\sigma_{crit} = \frac{\mu b \rho^{1/2}}{2}$$



Work Hardening and Recovery

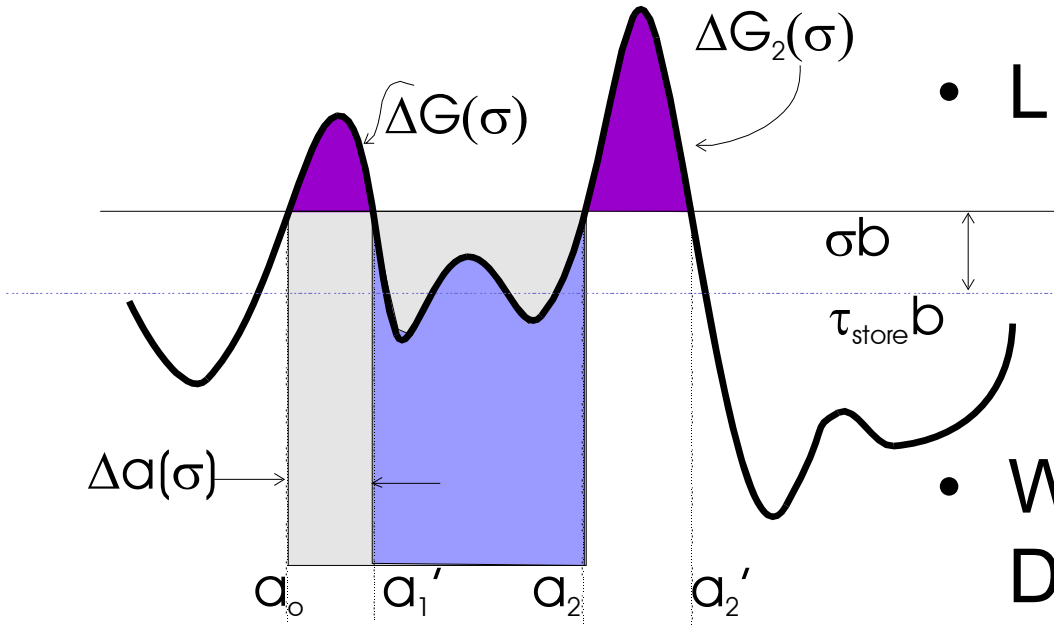
$$\frac{d\sigma}{dt} = \frac{d}{dt} [\sigma(\varepsilon(t), t)] = \left. \frac{\partial \sigma}{\partial \varepsilon} \right|_t \dot{\varepsilon} + \left. \frac{\partial \sigma}{\partial t} \right|_{\varepsilon}$$

$$\frac{d\sigma}{dt} = h\dot{\varepsilon} + r \quad \text{Bailey-Orowan Eq.}$$

- At steady state, hardening = recovery
- If square root of disl. dens. proportional to mean free path, $\lambda = a\rho^{1/2}$
and if density is a function of stress, $\sigma^2 = \alpha\mu b\rho^{1/2}$
then can show that $\frac{h}{\mu} = \frac{\alpha}{a}$

- | | | | | |
|-----|---------|----|-----|-----------------|
| Qtz | Olivine | W | FCC | Easy Glide |
| 1 | 1-3 | 50 | 350 | 10 ⁴ |

Thermodynamics of Glide and Climb



- Line glide resistance
Thermal activation
Applied Stress

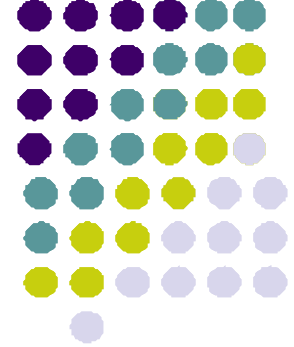
- Work done on mat'l.
Dissipated energy
Force on dislocation

Velocity Kinetics

$$\bar{v} = \frac{\Delta L}{t_g + t_o} \quad \text{where} \quad \begin{cases} \Delta L \text{ is distance to next obstacle} \\ t_g \text{ is time to glide} \\ t_o \text{ is time to overcome obstacle} \end{cases}$$

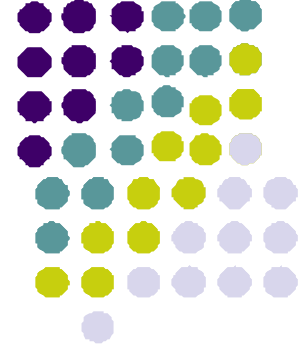
- If obstacle can be overcome by thermal activation
(e.g. lattice friction, cutting of soft ppt., unraveling attractive junctions)
 - $\Delta L \gg a_1 a_1'$ then $\Delta L = \lambda$ (where λ is the dislocation spacing)
 $t_g \ll t_o$ e.g. *Cross slip* in FCC metals
 - $\Delta L \cong a_1 a_1'$, obstacle met as soon as overcome,
Glide-controlled Creep
- Obstacles can't be overcome but may be avoided by climb,
Recovery-controlled Creep

Recovery Processes



- Recovery-removal of defects
 - Recovery processes
 - Collapse of dipoles
 - Loop collapse
 - Annihilation
 - Sub-grain boundary annihilation
 - Climb and glide to grain boundary, surface
 - Sub-grain boundary coarsening
- Recrystallization-creation and motion of high angle grain boundaries
 - Recrystallization Processes
 - Grain growth
 - Static recrystallization
 - Dynamic recrystallization
 - Chemically induced gb migration

Power Law Creep



$$\dot{\epsilon} = \epsilon_0 \nu_0 \frac{\mu \Omega}{kT} f(\mu_i)^{p_i} \left(\frac{\sigma}{\mu_{shear}} \right)^n \exp\left(-\frac{\Delta H}{kT} \right)$$

- n combined effect of density and mobility terms
- Fugacity and chemical potential of phases may affect dislocation mobility
- Debye frequency, shear modulus and molecular volume
- For specific models see *Kohlstedt et al.*, and *Al et Kohlstedt 95*.

Competition between Diffusion and Dislocation Creep

- Dislocation Creep:

$$\dot{\epsilon} = A_{xs} \sigma^2 \exp\left[-\frac{Q_{xs} [(1 - C_{xs} \sigma)]}{RT}\right]$$

- Diffusion Creep

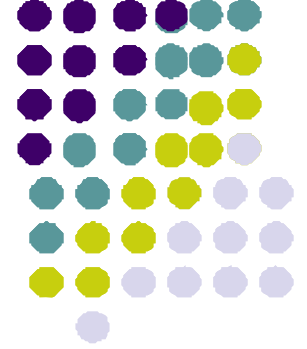
$$\dot{\epsilon} = A_{diff} \frac{\sigma}{d^m} \cdot \exp\left(-\frac{Q_{diff}}{RT}\right)$$

- Composite Flow (Ter Heege et al.)

$$\dot{\epsilon} = \dot{\epsilon}_{cs} V_{cs} + \dot{\epsilon}_{diff} V_{diff}$$

- State Variable: Grain size

Low Temperature High Stress Laws (Other Creep)



$$\dot{\varepsilon} = \dot{\varepsilon}_o \mathbf{exp} \left[-\frac{\Delta g}{kT} \left(1 - \frac{\sigma}{\tau} \right)^p \right]^q$$